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# ***Advances in Patterning Materials and Processes XXXVII***

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Daniel P. Sanders**  
*Editors*

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# Contents

vii	<i>Authors</i>
xi	<i>Conference Committee</i>

---

## INORGANIC RESISTS: JOINT SESSION WITH CONFERENCES 11323 AND 11326

---

11326 04	<b>All-new nickel-based Metal Core Organic Cluster (MCOC) resist for N7+ node patterning</b> [11326-3]
----------	-----------------------------------------------------------------------------------------------------------

---

## STOCHASTICS: JOINT SESSIONS WITH CONFERENCES 11323 AND 11326

---

11326 07	<b>Algebraic model for extremely unlikely resist dissolution events</b> [11326-6]
11326 09	<b>EUV chemically amplified resist component distribution and efficiency for stochastic defect control</b> [11326-8]

---

## NOVEL RESISTS

---

11326 0A	<b>EUV resist chemical gradient enhancement by UV flood exposure for improvement in EUV resist resolution, process control, roughness, sensitivity, and stochastic defectivity</b> [11326-9]
11326 0B	<b>Molecular resists equipped with fluorinated aromatic units for electron-beam and extreme UV lithography</b> [11326-10]
11326 0C	<b>High sensitivity non-CAR resists for EUV and EB lithography</b> [11326-11]
11326 0D	<b>Sensitivity enhancement of chemically amplified EUV resist by adding diphenyl sulfone derivatives</b> [11326-12]
11326 0E	<b>Explorations of missing hole defect in EUV patterning</b> [11326-13]

---

## FUNDAMENTALS AND MODELING

---

11326 0G	<b>Mechanism of resist heating effect in chemically amplified resist</b> [11326-15]
11326 0I	<b>A physics-driven complex valued neural network (CVNN) model for lithographic analysis</b> [11326-17]
11326 0J	<b>Infiltration synthesis of hybrid nanocomposite resists for advanced nanolithography</b> [11326-18]

---

## INTEGRATION

---

- 11326 OK **Defectivity modulation in EUV resists through advanced filtration technologies** [11326-102]
- 11326 OM **How to improve overlay of highly deformed 3D NAND wafers** [11326-20]
- 11326 ON **Challenges and opportunities of KrF photoresist development for 3D NAND application** [11326-21]
- 11326 OO **A DOE study of plasma etched microlens shape for CMOS image sensors** [11326-22]
- 11326 OP **Unique freeze cleaning technology** [11326-23]

---

## DEPOSITION-BASED PATTERNING

---

- 11326 OS **Sacrificial hardmask ALD with hydrogen peroxide: comparative study of low temperature growth and film characteristics for TiO<sub>2</sub> and Al<sub>2</sub>O<sub>3</sub>** [11326-27]

---

## NOVEL PATTERNING

---

- 11326 OX **Roughness study on line and space patterning with chemo-epitaxy directed self-assembly** [11326-31]
- 11326 OY **Defect mitigation of chemo-epitaxy DSA patterns** [11326-32]
- 11326 OZ **Establishing a sidewall image transfer chemo-epitaxial DSA process using 193 nm immersion lithography** [11326-33]

---

## SUPPLIER

---

- 11326 11 **Performance enhancements with high opacity multi-trigger resist** [11326-35]
- 11326 12 **Stochastic effects on EUV CAR systems: investigation of materials impact** [11326-36]
- 11326 13 **Addressing metallic contaminants in the photochemical supply chain** [11326-37]

---

## UNDERLAYERS

---

- 11326 14 **Improvement of EUV Si hardmask performance through wet chemistry functionalization** [11326-38]

- 11326 15 **Underlayer optimization method for EUV lithography** [11326-39]
- 11326 16 **Are surfaces of silicon hardmasks adaptive?** [11326-40]
- 11326 17 **Planarized spin-on carbon hardmask** [11326-41]
- 11326 18 **Highly substituted fullerene-based spin-on organic hardmasks** [11326-42]

---

**POSTER SESSION: EUV**

---

- 11326 19 **Consideration of missing defect suppression technique in EUV hole patterning** [11326-47]
- 11326 1C **Focusing on nanoparticles-based photomultiplier in n-CARs** [11326-65]

---

**POSTER SESSION: DIRECTED SELF-ASSEMBLY**

---

- 11326 1E **Block copolymers with a fluoro-block for 5 nm DSA patterning application** [11326-43]
- 11326 1I **Block copolymer line roughness measurement via PSD: application to fingerprint samples** [11326-66]
- 11326 1J **Expanding DSA process window with atmospheric control** [11326-103]
- 11326 1K **Understanding and mitigating bridge defects in block copolymer directed self-assembly through computational materials design and optimization** [11326-104]

---

**POSTER SESSION: UNDERLAYERS**

---

- 11326 1M **New poly-maleimide resin for SOC hardmask with high thermal stability** [11326-52]
- 11326 1N **Design considerations for high etch resistance spin-on carbon underlayers** [11326-57]
- 11326 1O **Development of planarizing spin-on carbon materials for high-temperature processes** [11326-61]
- 11326 1P **Super planarizing material for trench and via arrays** [11326-64]
- 11326 1Q **Defect mitigation and characterization in silicon hardmask materials** [11326-68]
- 11326 1R **Development of ion exchange purification for advanced materials contain siloxane polymer** [11326-71]

---

**POSTER SESSION: FUNDAMENTALS**

---

- 11326 1S     **Study of lithographic characteristics due to differences in novolac resin structure** [11326-44]
- 11326 1U     **Local condensation of TMAH developer at photoresist/glass interface analyzed by using confocal laser scanning microscope (CLSM)** [11326-56]
- 11326 1V     **Adhesion improvement of photoresist: destruction mode analysis** [11326-60]
- 11326 1W     **Fundamental study on lithographic characteristics of metal oxo clusters for KrF, ArF, and electron beam lithography** [11326-105]

---

**POSTER SESSION: INTEGRATION**

---

- 11326 1X     **A novel filter screening methodology for Si hardmask materials in EUV lithography** [11326-49]
- 11326 1Z     **Improving EUV underlayer coating defectivity using point-of-use filtration** [11326-58]
- 11326 20     **CD uniformity improvement for sub 20 nm DRAM process with negative tone development** [11326-63]
- 11326 22     **Marangoni effect-based under-layer for a dual Damascene via-first approach: a scalable solution to the unwanted photoresist swing effect** [11326-70]